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**Douglas J. Resnick
Christopher Bencher**
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Session Chairs

- 1 Alternative Lithography Keynote Session
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Christopher Benchner, Applied Materials, Inc. (United States)
- 2 DSA Process and Integration
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Lei Wen, HGST (United States)
- 3 Novel Nanolithography
Ivo W. Rangelow, Technische Universität Ilmenau (Germany)
Helmut Schiff, Paul Scherrer Institut (Switzerland)
- 4 Roll to Roll UV Nanoimprint Lithography
John G. Maltabes, Hewlett-Packard Laboratories (United States)
Laurent Pain, CEA-LETI (France)
- 5 Metrology and Inspection for Directed Self-Assembly: Joint Session with Conferences 9049 and 9050
Martha I. Sanchez, IBM Research - Almaden (United States)
Daniel J. C. Herr, The University of North Carolina at Greensboro (United States)
- 6 Beam Lithography
James A. Liddle, National Institute of Standards and Technology (United States)
Ines A. Stolberg, Vistec Electron Beam GmbH (Germany)
- 7 DSA Materials and Processes I: Joint Session with Conferences 9049 and 9051
Benjamin M. Rathsack, Tokyo Electron America, Inc. (United States)
Roel Gronheid, IMEC (Belgium)
- 8 DSA Materials and Processes II: Joint Session with 9049 and 9051
James A. Liddle, National Institute of Standards and Technology (United States)
Ralph R. Dammel, AZ Electronic Materials USA Corp. (United States)
- 9 Step and Repeat UV Nanoimprint Lithography
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)

- 10 Multiple Electron Beam Direct Write Lithography
Hans Loeschner, IMS Nanofabrication AG (Austria)
Frank E. Abboud, Intel Corporation (United States)
- 11 DSA Line Patterning
Frank M. Schellenberg, Consultant (United States)
- 12 Nanodevice Fabrication
Kevin T. Turner, University of Pennsylvania (United States)
- 13 DSA Design for Manufacturability: Joint Session with Conferences
9049, 9052, and 9053
Michael A. Guillorn, IBM Thomas J. Watson Research Center
(United States)
Bruce W. Smith, Rochester Institute of Technology (United States)
- 14 DSA Via Patterning
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